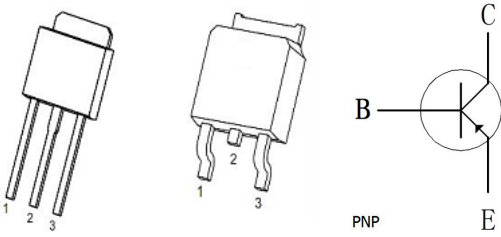


<p>TRANSISTOR (PNP)</p>	<p>TO-252/TO-251 Plastic-Encapsulate Transistors</p>																																										
<p><u>TO-252/TO-251</u></p>  <p>1.BASE 2.COLLECTOR 3.EMITTER</p> <p>Marking :B772M</p>	<p>Features</p> <ul style="list-style-type: none"> • power switching applications 																																										
<p>MAXIMUM RATINGS (Ta=25°C unless otherwise noted)</p> <table border="1" style="width: 100%; border-collapse: collapse;"> <thead> <tr> <th style="text-align: center;">Parameter</th> <th style="text-align: center;">Symbol</th> <th style="text-align: center;">Value</th> <th style="text-align: center;">Unit</th> </tr> </thead> <tbody> <tr> <td>Collector-Base Voltage</td> <td style="text-align: center;">VCBO</td> <td style="text-align: center;">-40</td> <td style="text-align: center;">V</td> </tr> <tr> <td>Collector-Emitter Voltage</td> <td style="text-align: center;">VCEO</td> <td style="text-align: center;">-30</td> <td style="text-align: center;">V</td> </tr> <tr> <td>Emitter-Base Voltage</td> <td style="text-align: center;">VEBO</td> <td style="text-align: center;">-6</td> <td style="text-align: center;">V</td> </tr> <tr> <td>Collector Current -Continuous</td> <td style="text-align: center;">IC</td> <td style="text-align: center;">-3</td> <td style="text-align: center;">A</td> </tr> <tr> <td>Collector Current -Pulsed</td> <td style="text-align: center;">ICM</td> <td style="text-align: center;">2</td> <td style="text-align: center;">A</td> </tr> <tr> <td>Collector Power Dissipation</td> <td style="text-align: center;">PC</td> <td style="text-align: center;">1.25</td> <td style="text-align: center;">W</td> </tr> <tr> <td>Thermal Resistance From Junction To Ambient</td> <td style="text-align: center;">RθJA</td> <td style="text-align: center;">125</td> <td style="text-align: center;">°C/W</td> </tr> <tr> <td>Junction Temperature</td> <td style="text-align: center;">Tj</td> <td style="text-align: center;">150</td> <td style="text-align: center;">°C</td> </tr> <tr> <td>Storage Temperature</td> <td style="text-align: center;">Tstg</td> <td style="text-align: center;">-55~+150</td> <td style="text-align: center;">°C</td> </tr> </tbody> </table>				Parameter	Symbol	Value	Unit	Collector-Base Voltage	VCBO	-40	V	Collector-Emitter Voltage	VCEO	-30	V	Emitter-Base Voltage	VEBO	-6	V	Collector Current -Continuous	IC	-3	A	Collector Current -Pulsed	ICM	2	A	Collector Power Dissipation	PC	1.25	W	Thermal Resistance From Junction To Ambient	RθJA	125	°C/W	Junction Temperature	Tj	150	°C	Storage Temperature	Tstg	-55~+150	°C
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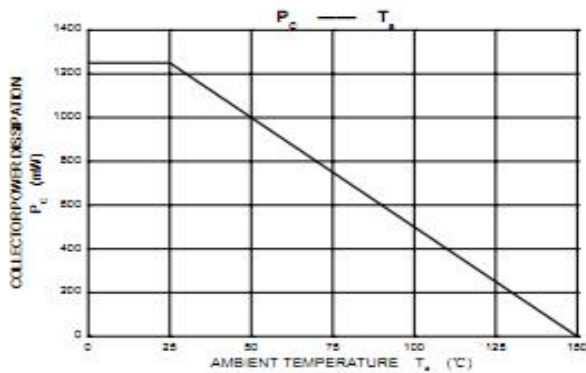
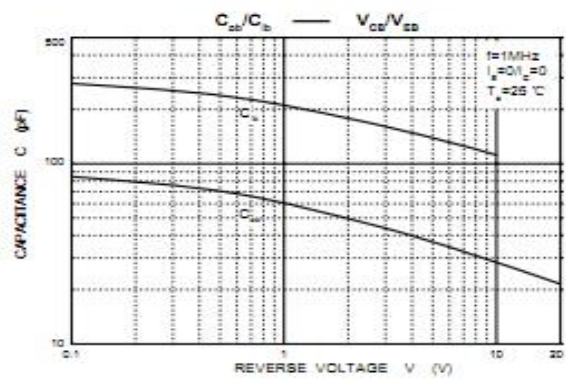
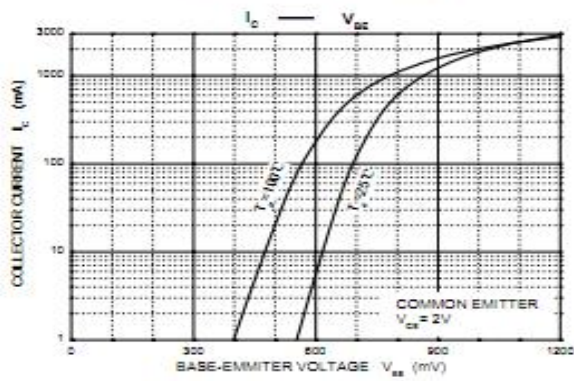
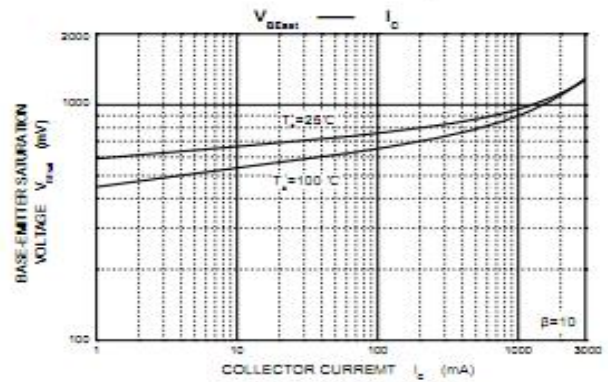
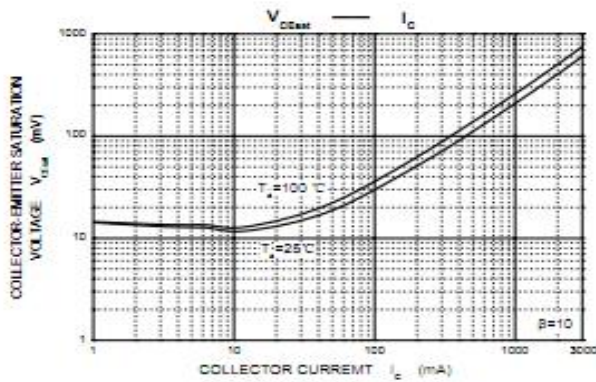
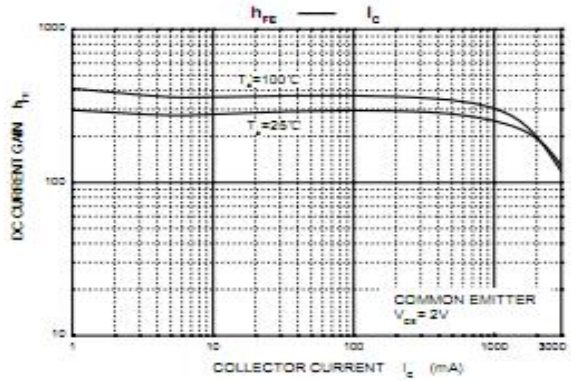
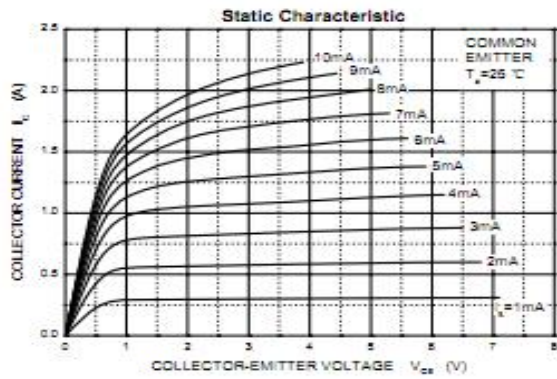
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= -100µA, IE=0	-40			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -10mA, IB=0	-30			V
Emitter-base breakdown voltage	V(BR)EBO	IE= -100µA, IC=0	-6			V
Collector cut-off current	ICBO	VCB= -40 V , IE=0			-1	µA
Collector cut-off current	ICEO	VCB= -30V , IE=0			-10	µA
Emitter cut-off current	IEBO	VEB= -6V , IC=0			-1	µA
DC current gain	hFE	VCE= -2V, IC= -1A	60		400	
	hFE	VCE= -2V, IC= -500mA	100			
Collector-emitter saturation voltage	VCE(sat)	IC= -2A, IB= -0.2A			-0.5	V
Base-emitter saturation voltage	VBE(sat)	IC= -2A, IB= -0.2A			-1.5	V
Transition frequency	fT	VCE= -5V, IC= -0.1A f=1MHz	50	80		MHz
Fall time	tf	IC=-1A, IB1=-IB2=- 0.2A VCC=100V			0.5	µs
Storage time	ts		1.5		4	µs

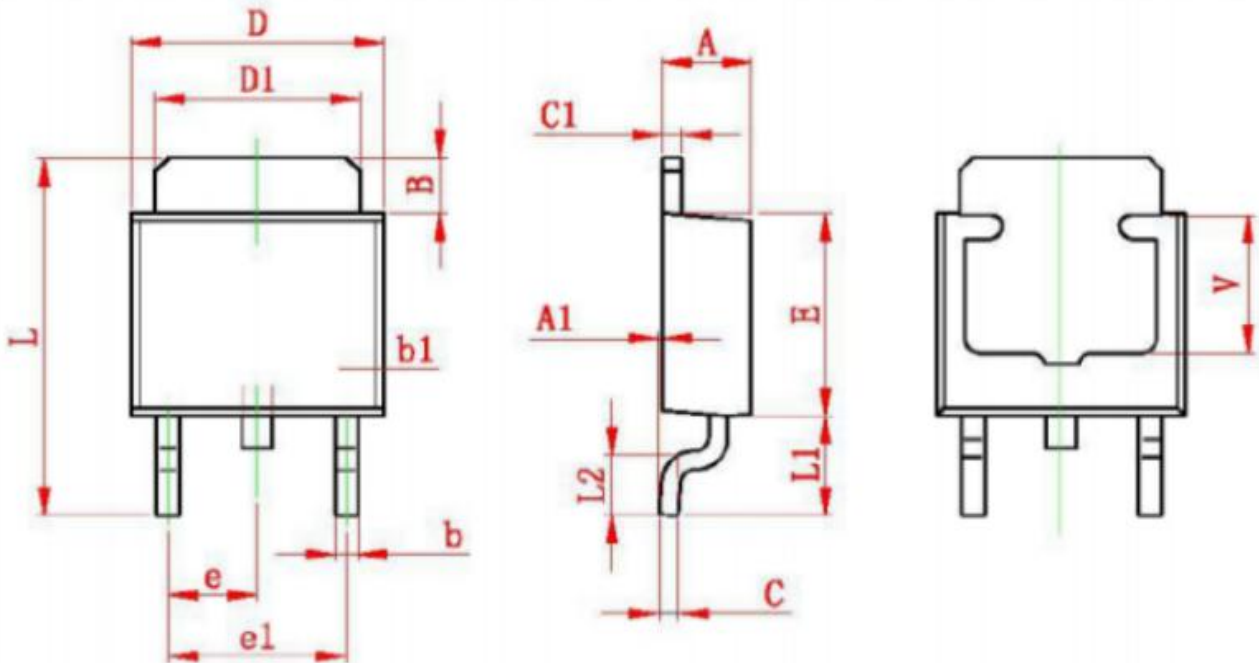
CLASSIFICATION OF hFE

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

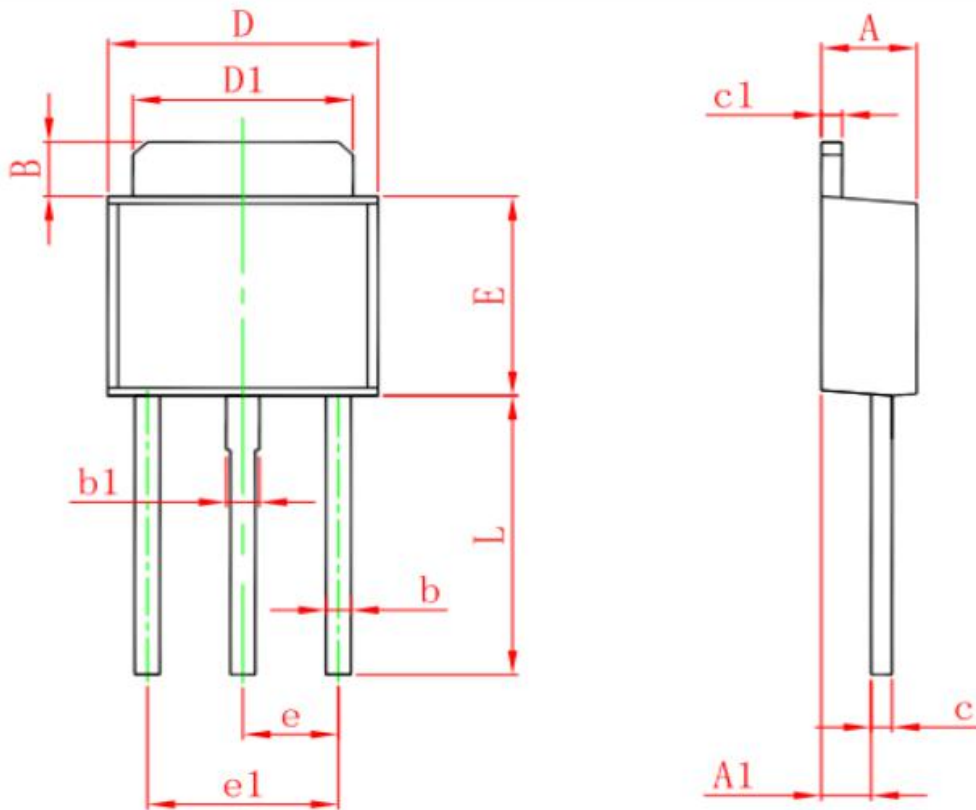


TO-252 PACKAGA OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP		0.091 TYP	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
V	3.80 REF		0.150 REF	

TO-251 PACKAGA OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	1.050	1.350	0.042	0.054
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	7.500	7.900	0.295	0.311

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)